

Weebit Nano technical parameters demonstrate results at forefront of ReRAM market

1 May 2019 – Weebit Nano (ASX: WBT), the Israel-based semiconductor company seeking to develop and commercialise the next generation of memory technology, is pleased to announce that its Silicon Oxide (SiOx) ReRAM technical parameters have been confirmed at the forefront of the market.

This builds on the recent process optimisation milestones where Weebit Nano announced it had reached market level retention in October 2018, and market level endurance and voltages in January 2019.

The key parameters for a non-volatile memory are retention and endurance. Tests on the latest batch of wafers conducted by Leti, the French research institute recognised as a global leader in the field of micro-electronics, have shown significant improvement on the previous results, demonstrating retention of over 10 years at 130-150°C – at the forefront of ReRAM technologies. These results at very high temperatures broaden the range of potential commercial applications for the Company's ReRAM technology, most notably automotive applications.

In addition, the latest batch showed single cells demonstrating endurance of a million cycles, significantly exceeding state-of-the-art flash performance.

Coby Hanoach, CEO of Weebit Nano, said: "Improving technical parameters is an ongoing task. As announced previously, we demonstrated market competitive retention, endurance and voltage levels early this year. We are now very proud to have improved the endurance and the retention at high temperatures, placing us at the forefront of the ReRAM market. These capabilities in our ReRAM chips also opening new potential markets such as automotive. This is a significant step forward for the company.

"We will continue to optimise parameters, responding to feedback from potential customers as part of our ongoing dialogue with them. This will be done in parallel to the work on productisation, as these two tasks go hand-in-hand."

Weebit Nano is continuing to optimise its technology as it moves towards production on 300mm wafers and will report further technical achievements as they are made.

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About Weebit Nano Limited

Weebit Nano is a leader in the development of next generation computer memory technology, and plans to become the new industry standard in this space. Its goal is to address the growing need for a significantly higher performance and lower power computer memory technology. Weebit Nano's ReRAM technology is based on fab-friendly Silicon Oxide, allowing the company to rapidly execute, without the need for special equipment or preparations. The company secured several patents to ensure optimal commercial and legal protection for its ground-breaking technology.

Weebit Nano's technology enables a quantum leap, allowing semiconductor memory elements to be significantly cheaper, faster, more reliable and more energy efficient than the existing Flash technology. Weebit Nano has signed an R&D agreement with Leti, an R&D institute that specialises in nanotechnologies, to further develop SiOx ReRAM technology.

For more information please visit: <http://www.weebit-nano.com/>



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